

42. The method according to claim 40, further comprising providing a guide line on the substrate and correcting the cutting position using the guideline.

43. The method according to claim 40, wherein the slice line comprises an electrode layer constituting the thin film semiconductor element.

REMARKS

Applicants request favorable reconsideration and allowance of the subject application in view of the preceding amendments and the following remarks.

Claims 35-43 are presented for consideration. Claims 35 and 40 are independent. Claim 35 has been amended to clarify features of the subject invention. Support for this change can be found in the original application as filed. Therefore, no new matter has been added.

In the above-noted Office Action, the Examiner asserted that the Amendment filed on July 23, 2002, is not fully responsive to the prior Office Action because, as the Examiner asserts, the new claims, particularly new claims 35-39, appear to be directed to a patentably distinct invention which had not previously been examined. The Examiner requested that these claims be amended so that they are directed to the invention previously examined in this application, that is, to be directed to a method of cutting a substrate. To expedite prosecution of this application, Applicants have so amended independent claim 35. Therefore, claim 35, as well as claims 36-39 depending therefrom, are directed to a method of cutting a substrate of a


semiconductor device. The Examiner will further note that claims 40-43 likewise are directed to various aspects of a method of cutting a substrate of a semiconductor device. Accordingly, Applicants submit that all the claims currently presented are directed to various aspects of methods of cutting a substrate. Applicants further submit that this response, together with the Amendment filed on July 23, 2002, are fully responsive to the prior Office Action.

In addition, Applicants submit that claims 35-43 patentably define features of the subject invention, at least for the reasons presented in Applicants' prior response, with the caveat that the preamble of independent claim 35 is now directed to a method of cutting a substrate, as requested by the Examiner.

Applicants further submit that the instant application is in condition for allowance. Favorable reconsideration and an early Notice of Allowance are also requested.

Applicants' undersigned attorney may be reached in our Washington, D.C. office by telephone at (202) 530-1010. All correspondence should be directed to our address listed below.

Respectfully submitted,



Attorney for Applicants
Steven E. Warner
Registration No. 33,326

FITZPATRICK, CELLA, HARPER & SCINTO
30 Rockefeller Plaza
New York, New York 10112-3801
Facsimile: (212) 218-2200
SEW/eab

APPENDIX A

IN THE CLAIMS

35. (Amended) A method of [producing] cutting a substrate of a semiconductor device constructed by arranging a plurality of substrates, on each of which, thin film semiconductor elements two-dimensionally arranged are installed, said method comprising the steps of:

cutting a substrate along at least a slice line provided on the substrate and on a side facing another substrate, which is one of the substrates when the plurality of substrates are arranged, while detecting a misalignment of a cutting position from the slice line and correcting a cutting position;

cutting the substrate of a side opposing the slice line without correcting the cutting position; and

adjacently arranging the plurality of substrates on substantially a same plane such that the sides having been cut face each other, while correcting the cutting position of the substrates.